

CCM1095 20 TO 1000 MHz HIGH POWER AMPLIFIER

Typical Values

High Output Power	+38 dBm
Broad Bandwidth	20-1000 MHz
High Third Order I.P.	+49 dBm

High Performance Thin Film for RF Section
Includes Bias Sequencer

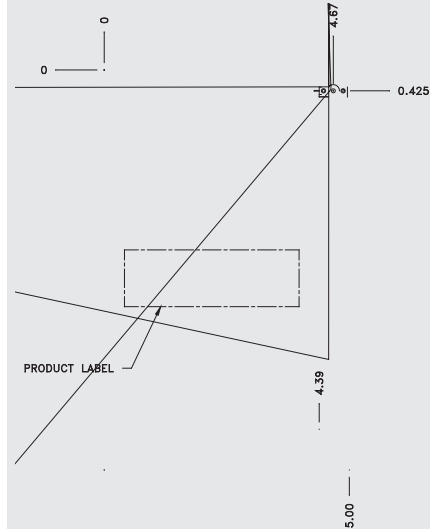
CCM1095

CCM1095

SPECIFICATIONS*

Parameter	Typical	Guaranteed	
		0 to 50° C	-55 to +85° C
Frequency (Min.)		10-1200 MHz	20-1000 MHz
Small Signal Gain (Min.)	11.3 dB	10.5 dB	10.0 dB
Gain Flatness (Max.)	±0.5 dB	±0.7 dB	±0.8 dB
Noise Figure (Max.)			
	50-100 MHz	4.5 dB	5.2 dB
	100-1000 MHz	4.0 dB	4.7 dB
SWR (Max.)	Input/Output	1.7:1	2.0:1
			2.0:1
Power Output (Min.) [^]			
	@ 1dB comp. 20-70 MHz	+37.0 dBm	+36.0 dBm
	70-1000 MHz	+38.0 dBm	+37.0 dBm
Reverse Isolation	18.0 dB	—	—
DC Current (Max.)	500 mA	520 mA	530 mA

* Measured in a 50-ohm system at +36 Vdc unless otherwise specified.
^ Output Power averages 1.5 dBm less using +28 Vdc.



INTERMODULATION PERFORMANCE

ABSOLUTE MAXIMUM RATINGS

Storage Temperature	-65 to 150° C
Maximum Case Temperature	+125° C
Maximum DC Voltage	+40 Volts
Maximum Continuous RF Input Power	+30 dBm
Maximum Short Term Input Power (1 Minute Max.)	+33 dBm
Maximum Peak Power (3 µsec Max.)	+35 dBm
Burn-in Temperature	105° C
Thermal Resistance ¹ (θjc)	+5 C/Watt
Junction Temperature Rise Above Case (Tjc)	+28 V
.....	+36 V
.....	+70° C
.....	+90° C

¹ Thermal resistance is based on total power dissipation.

DIMENSIONS ARE IN INCHES (MILLIMETERS)

TYPICAL PERFORMANCE

